NSN 5962-01-374-8582

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-374-8582

Maximum	Power	Dissin	ation	Rating:
IVIAXIIIIUIII	rowei	DISSID	auon	Raunu.

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

An/tyq-2 (v) 1 e/i fscm 13973

Features Provided:

Electrostatic sensitive and monolithic and programmed and ultraviolet erasable and w/heat sink

Inclosure Configuration:

Dual-in-line

Output Logic Form:

N-type metal oxide-semiconductor logic

Case Outline Source And Designator:

D-3 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit digital, nmos 4kx8 uv erasable prom

Voltage Rating And Type Per Characteristic:

-0.3 volts total supply and 6.0 volts total supply

Time Rating Per Chacteristic:

250.00 nanoseconds af output megawatts

Memory Device Type:

Eprom

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Specification Data:

67268-8001203ja government standard

Purchase Description Identification:

1397-32-475-0316

Departure From Cited Document:

Altered by programming & marking

Shelf Life:

N/a

Unit Of Measure:

NSN 5962-01-374-8582

Memory Microcircuit - Page 2 of 2



Demilitarization:

Yes - demil/mli

Fiig:

A458a0